

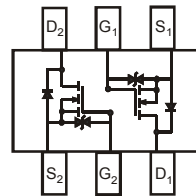
Features

- Dual N-Channel MOSFET
- Low On-Resistance (1.0V max)
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **ESD Protected up to 2kV**
- **"Green" Device (Note 4)**
- **Qualified to AEC-Q101 standards for High Reliability**


ESD protected up to 2kV


TOP VIEW

SOT-363


 TOP VIEW
Internal Schematic

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	50	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current (Note 1)	I_D	Continuous	305
		Pulsed (Note 3)	800

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P_D	250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV_{DSS}	50	—	—	V	$V_{GS} = 0V, I_D = 10\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	60	nA	$V_{DS} = 50V, V_{GS} = 0V$
Gate-Body Leakage	I_{GSS}	—	—	1	μA	$V_{GS} = \pm 12V, V_{DS} = 0V$
				500	nA	$V_{GS} = \pm 10V, V_{DS} = 0V$
				50	nA	$V_{GS} = \pm 5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(th)}$	0.49	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	3.0	Ω	$V_{GS} = 1.8V, I_D = 50\text{mA}$
				2.5	Ω	$V_{GS} = 2.5V, I_D = 50\text{mA}$
				2.0	Ω	$V_{GS} = 5.0V, I_D = 50\text{mA}$
On-State Drain Current	$I_{D(on)}$	0.5	1.4	—	A	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance	$ Y_{fs} $	200	—	—	mS	$V_{DS} = 10V, I_D = 0.2A$
Source-Drain Diode Forward Voltage	V_{SD}	0.5	—	1.4	V	$V_{GS} = 0V, I_S = 115\text{mA}$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	—	50	pF	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	5.0	pF	

- Notes:
1. Device mounted on FR-4 PCB.
 2. No purposefully added lead.
 3. Pulse width $\leq 10\mu\text{s}$, Duty Cycle $\leq 1\%$.
 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 5. Short duration pulse test used to minimize self-heating effect.

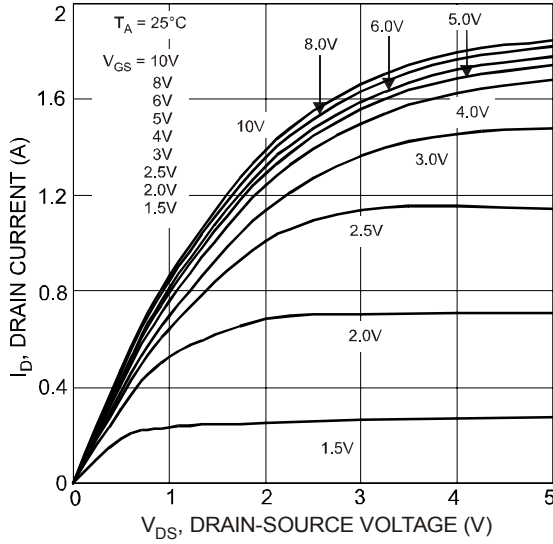


Fig. 1 Typical Output Characteristics

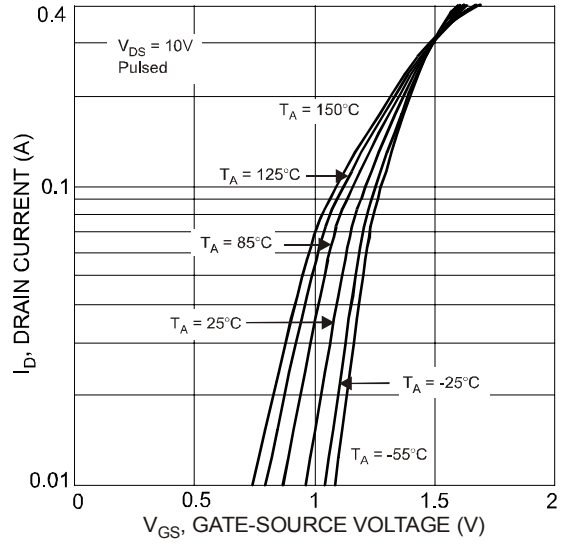


Fig. 2 Typical Transfer Characteristics

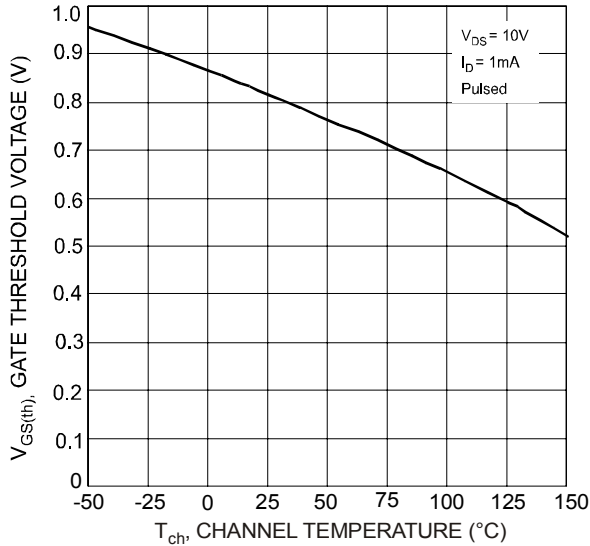


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

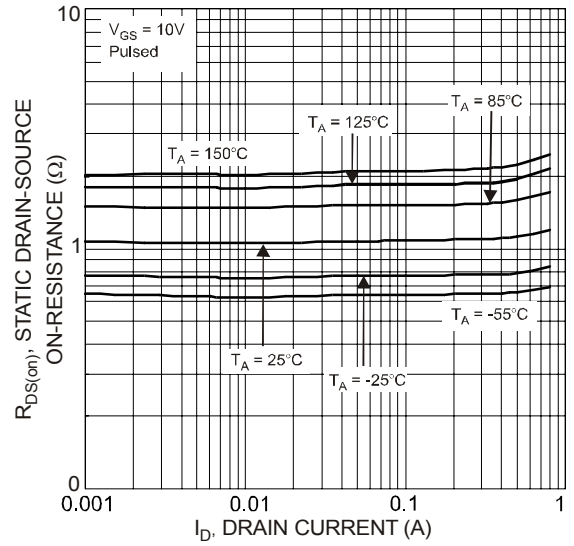


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

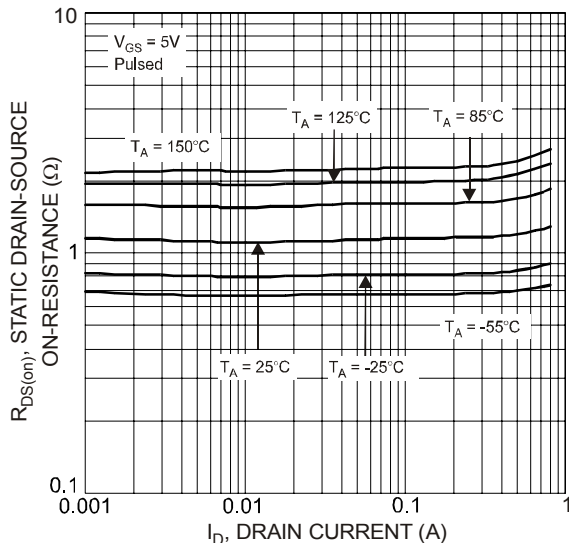


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

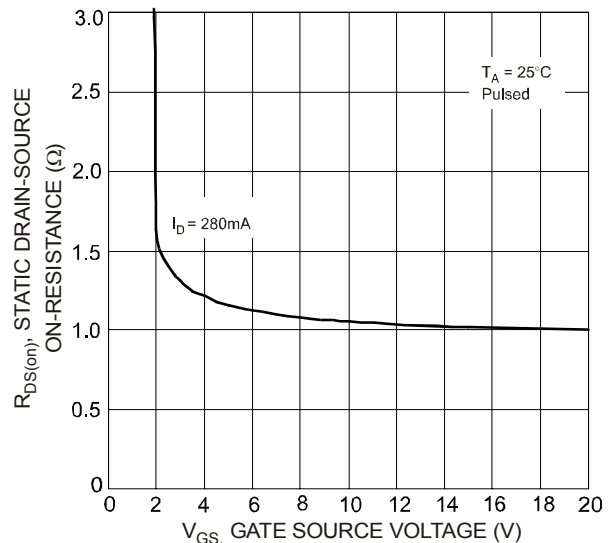


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

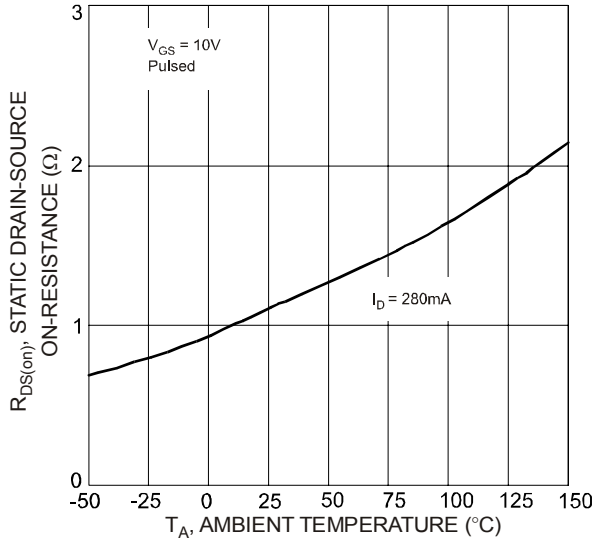


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

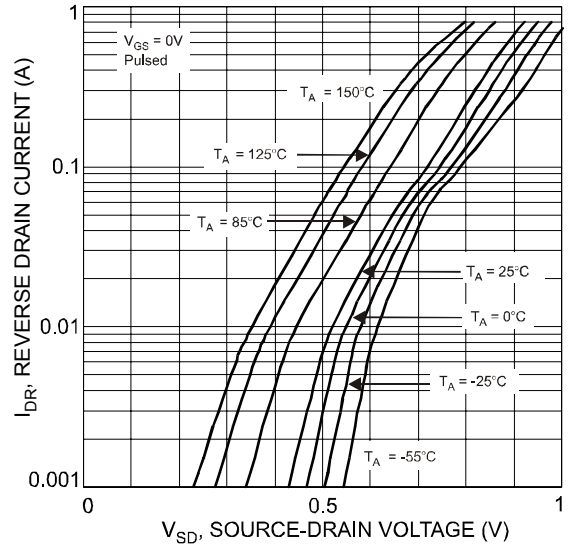


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

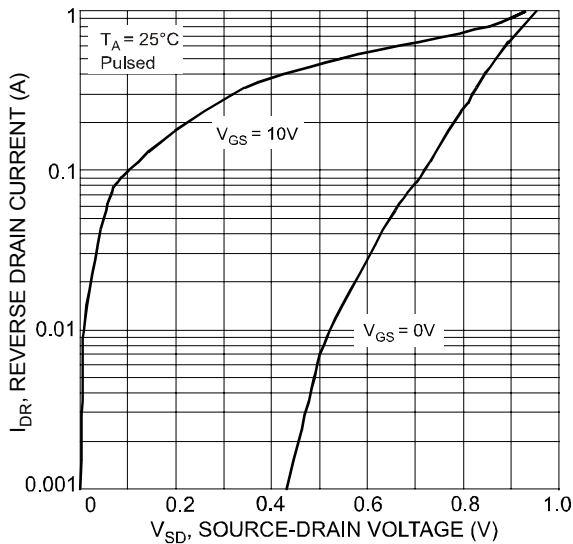


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

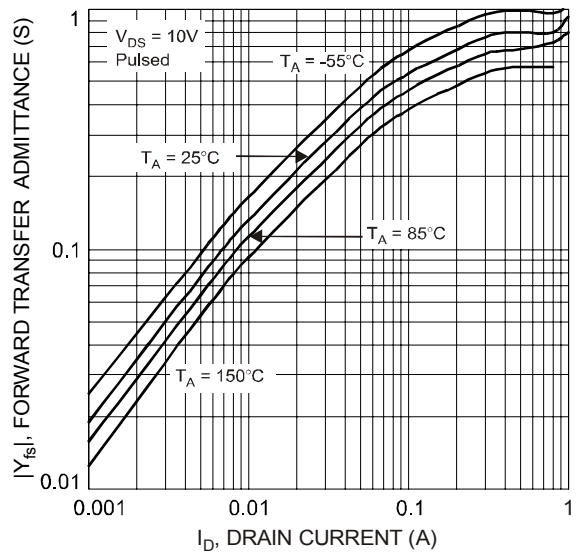


Fig. 10 Forward Transfer Admittance vs. Drain Current

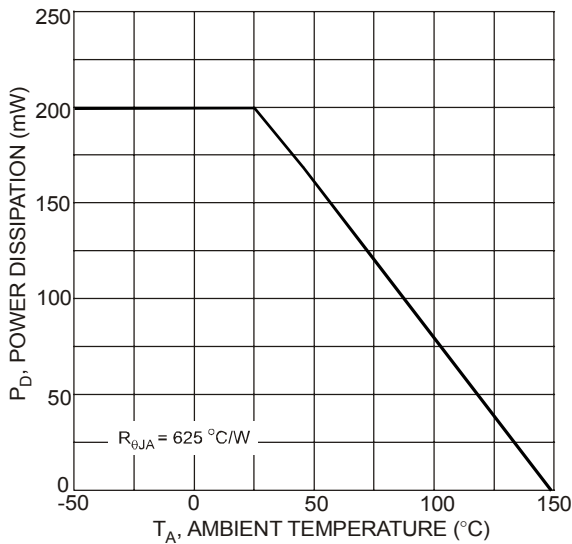


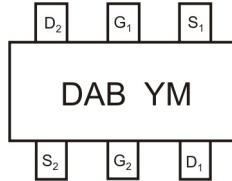
Fig. 11 Derating Curve - Total

Ordering Information (Note 6)

Part Number	Case	Packaging
DMN5L06DWK-7	SOT-363	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



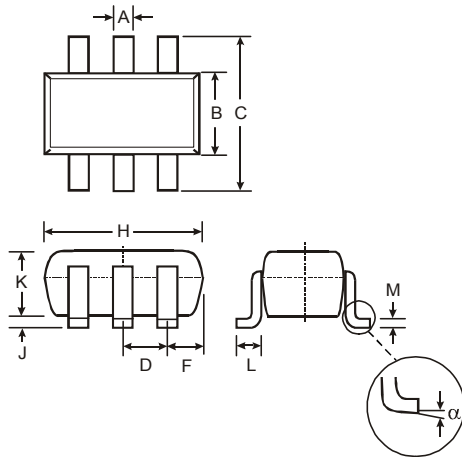
DAB = Marking Code
YM = Date Code Marking
Y = Year ex: T = 2006
M = Month ex: 9 = September

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012
Code	T	U	V	W	X	Y	Z

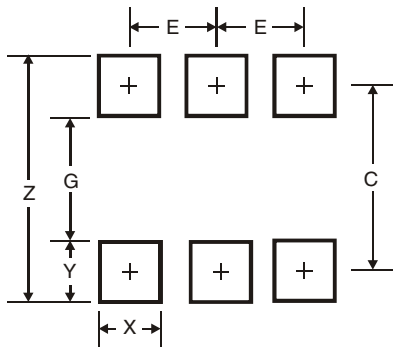
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C	1.9
E	0.65

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